
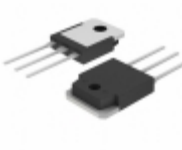
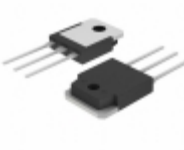
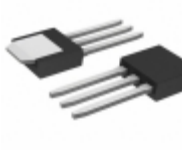



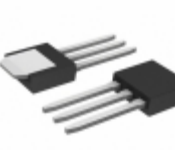
	<h2 style="color: red;">GP2M010A060F</h2>	
	Hersteller-Teilenummer:	GP2M010A060F
	Hersteller / Marke:	Global Power Technologies Group
	Teil der Beschreibung:	MOSFET N-CH 600V 10A TO220F
Datenblätter:	 GP2M010A060F.pdf	
RoHs Status:	Bleifrei / RoHS-konform	
Lagerzustand:	New original, 1883 pcs Stock Available.	
Liefern von:	Hong Kong	
Versandweg:	DHL/Fedex/TNT/UPS/EMS	
<p>Image may be representation. See specs for product details.</p>		

Spezifikationen

Teilenummer	GP2M010A060F
Hersteller	Global Power Technologies Group
Beschreibung	MOSFET N-CH 600V 10A TO220F
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	1883 pcs Stock
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Through Hole
Verpackung / Gehäuse	TO-220-3 Full Pack
Supplier Device-Gehäuse	TO-220F
Verlustleistung (max)	52W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	600V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	10A (Tc)
Rds On (Max) @ Id, Vgs	700 mOhm @ 5A, 10V
VGS (th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	35nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	1660pF @ 25V
Verpackung	Tube

GP2M010A060F ist neu im Original. Suche GP2M010A060F Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie GP2M010A060F Global Power Technologies Group mit Garantie und Vertrauen. Anfrage GP2M010A060F: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>GP2M008A060HG Global Power Technologies Group MOSFET N-CH 600V 7.5A TO220</p>	 <p>GP2M009A090NG Global Power Technologies Group MOSFET N-CH 900V 9A TO3PN</p>	 <p>GP2M011A090NG Global Power Technologies Group MOSFET N-CH 900V 11A TO3PN</p>	 <p>GP2M008A060PGH Global Power Technologies Group MOSFET N-CH 600V 7.5A IPAK</p>
 <p>GP2M010A065F Global Power Technologies Group MOSFET N-CH 650V 9.5A TO220F</p>	 <p>GP2M009A090FG Global Power Technologies Group MOSFET N-CH 900V 9A TO220F</p>	 <p>GP2M012A060F Global Power Technologies Group MOSFET N-CH 600V 12A TO220F</p>	 <p>GP2M008A060PG Global Power Technologies Group MOSFET N-CH 600V 7.5A IPAK</p>

heiße Teile

Mehr

⚙ GP200MTR-G1	↔ GP2A231LRSA	⇒ GP2A25J0000F	D GP2A25J0000F	↔ GP2A25NJ
⊣ GP2A28A1J00F	⚙ GP2A28N1J00F	D GP2AP002A00F	⇒ GP2AP002S00F	↔ GP2AP003A10F
⚙ GP2AP007A00F	⊣ GP2AP008T00F	⚙ GP2AP030A00F	↔ GP2AP052A00F	↔ GP2AP052A00F
D GP2L26K2	⚙ GP2M002A060FG	⊣ GP2M004A060PG	⚙ GP2M004A065FG	↔ GP2M004A065PG
⇒ GP2M005A050PG	↔ GP2M005A060CG	⚙ GP2M005A060FG	⊣ GP2M005A060PGH	↔ GP2M008A060FGH
↔ GP2M010A065F	⇒ GP2M011A090NG	D GP2M012A080NG	⚙ GP2M020A050H	⊣ GP2M020A060N
⚙ GP2S24J0000F	D GP2S27T3	⇒ GP2S27T3J00F	↔ GP2S27V6	↔ GP2S29SVJ00F
⊣ GP2S40JJ000F	⚙ GP2S700HCP	↔ GP2S700HCP	⇒ GP2W0004YP	↔ GP2W0110YPS
⚙ GP2W0112YPOF	⊣ GP2W0118YPS	⚙ GP2W0150YP0F	D GP2W3104XP0F	↔ GP2W3104YP0F
↔ GP2W3106YP0F	⚙ GP2W3152YP0F	⊣ GP2W3172XP0F	⚙ GP2W3270XP0F	↔ GP2Y0A02YK0F

Contact us: Info@Y-IC.com

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